## NSN 5961-00-306-7232

No Fiig: A110a0

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View Online at https://aerobasegroup.com/nsn/5961-00-306-7232 **Inclosure Material:** Ceramic all transistor and metal all transistor **Overall Length:** 0.725 inches all transistor **Mounting Facility Quantity:** 2 all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Unthreaded hole all transistor **Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 70.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter all transistor **Current Rating Per Characteristic:** 100.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 100.0 watts large-signal input power, common-emitter universal all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction all transistor **Test Data Document:** 12338-44817-00 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 4 ribbon all transistor Shelf Life: N/a **Unit Of Measure: Demilitarization:**